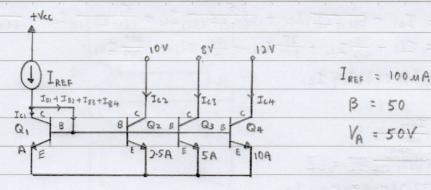
Esmund Lim

A.E Tutorial 10

1)



$$I_{c} = I_{s} e^{\left(\frac{V_{BE}}{V_{T}}\right)} \left(1 + \frac{V_{CE}}{V_{A}}\right) f V_{A} = \infty \text{ (ideal)}$$

$$\Rightarrow I_{c} \text{ will not be dependent on } V_{CE}$$

$$\Rightarrow I_{s} \propto \text{Area of emitter}$$

able to control Is directly -> affect the Ic

\* B of transistor, in small signal amplifier, assume B is fixed but in actual fact the transistor B do change with VCE  $B_i = B \left( 1 + \frac{VCE_i}{VC} \right)$ 

since all 4 BJT have the same

VBE, Ic will only be controlled

by Is which is also proportional

to Area of emitter (ideally)

also if all the transistor has infinite B

IB=0 (Ic=BIB, IB=Ie|B), Ic=IREB

The outcome is not the predicted value

it means that O VA \$\pm\$ \$\infty\$

@ Ie + IREF because there is IB

$$I_c = I_s e^{\left(\frac{V_{BE}}{V_T}\right)} \left(1 + \frac{V_{CE}}{V_A}\right)$$
 and  $I_s \propto A$ 

$$V_{BEI} = V_{BE2} = V_{BE3} = V_{BE4}$$

all the transistor will be in the forward active region

$$I_{C2} = \frac{A_2 e^{\left(\frac{V_{6E2}}{V_T}\right)} \left(1 + \frac{V_{CE2}}{V_A}\right)}{A_1 e^{\left(\frac{V_{5E1}}{V_T}\right)} \left(1 + \frac{V_{CE1}}{V_A}\right)}$$

$$= A_2 \left(1 + \frac{V_{CE2}}{V_A}\right)$$

$$A_1 \left(1 + \frac{V_{CE1}}{V_A}\right)$$

$$I_{C2} = \frac{A_2 \left(1 + \frac{V_{CE1}}{V_A}\right)}{A_1 \left(1 + \frac{V_{CE1}}{V_A}\right)} I_{C1}$$

However IREF # Ic1 Unlike in the case of Mosfet current mirrors because of base currents

$$I_{REF} = I_{C1} + I_{B1} + I_{B2} + I_{B3} + I_{B4}$$

$$= I_{C1} + \frac{I_{C1}}{\beta_{1}} + \frac{I_{C2}}{\beta_{2}} + \frac{I_{C3}}{\beta_{3}} + \frac{I_{C4}}{\beta_{4}}$$

$$= I_{C1} + \frac{I_{C1}}{\beta_{1}} + \frac{A_{2}(1 + \frac{V_{CE1}}{V_{A}}) I_{C1}}{\beta_{2}} + \frac{A_{3}(1 + \frac{V_{CE3}}{V_{A}}) I_{C1}}{A_{1}(1 + \frac{V_{CE1}}{V_{A}})} + \frac{A_{3}(1 + \frac{V_{CE3}}{V_{A}}) I_{C1}}{A_{1}(1 + \frac{V_{CE1}}{V_{A}})}$$

$$+ \frac{A_{4}(1 + \frac{V_{CE1}}{V_{A}}) I_{C1}}{A_{1}(1 + \frac{V_{CE1}}{V_{A}})} + \frac{A_{1}(1 + \frac{V_{CE1}}{V_{A}}) I_{C1}}{A_{1}(1 + \frac{V_{CE1}}{V_{A}})}$$

$$= I_{C1} + \frac{I_{C1}}{\beta_{1}} + \frac{A_{2}I_{C1}}{A_{2}I_{C1}} + \frac{A_{3}I_{C1}}{A_{3}I_{C1}} + \frac{A_{4}I_{C1}}{A_{4}I_{C1}}$$

$$= I_{C1} + \frac{I_{C1}}{V_{A}} + \frac{A_{2}I_{C1}}{V_{A}} + \frac{A_{3}I_{C1}}{V_{A}} + \frac{A_{4}I_{C1}}{V_{A}}$$

$$= I_{C1} + \frac{I_{C1}}{V_{A}} + \frac{A_{2}I_{C1}}{V_{A}} + \frac{A_{3}I_{C1}}{V_{A}} + \frac{A_{4}I_{C1}}{V_{A}} + \frac{A_{4}I_{C1}}{V_{A}}$$

Since VCEI = VBEI = 0.7V (forward active region)

No .

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$$I_{REF} = I_{c1} + \frac{10}{50(1+\frac{0.7}{50})}I_{c1} + \frac{2.5}{1(1+\frac{0.7}{50})(50)}I_{c1} + \frac{5}{1(1+\frac{0.7}{50})(50)}I_{c1} + \frac{10}{1(1+\frac{0.7}{50})(50)}I_{c1} + \frac{10}{1(1+\frac{0.7}{50})(50)}I_{c1}$$

= 73.26589595 X10-6 A

≈ 73.3 uA

$$I_{C2} = \frac{A_2(1+\frac{V_{CE_2}}{V_A})}{A_1(1+\frac{V_{CE_1}}{V_A})} I_{C1} \qquad \Gamma_{02} = \frac{V_A + V_{CE_2}}{I_{C2}} \\
= \frac{2.5(1+\frac{10}{50})}{1(1+\frac{50}{50})}.73.3 \text{ MA} \qquad = \frac{50+10}{216.76 \text{ MA}} \\
= 216.7630058 \times 10^{-6} \text{ A} \qquad = 276.8 \text{ Kg.}$$

$$I_{c3} = \frac{A_3(1+\frac{\sqrt{c}}{\sqrt{A}})}{A_1(1+\frac{\sqrt{c}}{\sqrt{A}})} I_{c1} \qquad f_{o3} = \frac{\sqrt{A}+\sqrt{c}E_3}{I_{c3}}$$

$$= \frac{5(1+\frac{2}{50})}{1(1+\frac{0}{50})} .73.3 \text{ MA} \qquad = \frac{50+9}{419.08\text{MA}}$$

$$= 419.0751445 \times 10^{-6} \text{ A} \qquad = 138.4 \text{ kg}$$

≈ 419.08MA

≈ 216.76 MA

$$I_{C4} = \frac{A_{4} \left(1 + \frac{V_{CE4}}{V_{A}}\right)}{A_{1} \left(1 + \frac{V_{CE4}}{V_{CE4}}\right)} I_{C1} \qquad \Gamma_{O4} = \frac{V_{A} + V_{CE4}}{I_{C4}}$$

$$= \frac{10 C 1 + \frac{12}{50}}{I \left(1 + \frac{9.7}{50}\right)} 73.3 \mu A \qquad = \frac{50 + 12}{895.9537572 \times 10^{-6}} A \qquad = 69.2 \text{ kg}$$

≈ 895.95MA

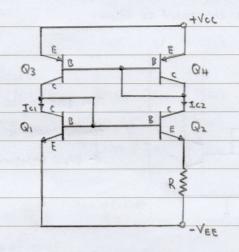
Note that the accuracy of the current mirror is dependent on B, Va and the number of mirror transistors connected to the same diode-connected transistor

-> more base current , less accurate

-> Mos don't have this problem -> no gate current

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2)



AES = 10 AEH

AE2 = 10 AE1

R=1K-2

B -> 00

ignore Early effect

Since B -> 00 , no IB

Ici = Ic3

Ic2 = Ic4

ignore Early effect

$$I_c = I_s e^{\left(\frac{\sqrt{g_E}}{\sqrt{T}}\right)}$$

Since AE3 = 10AE4

Ic3 = 10 Ic4

since Icz=Ici

Ic1 = 10 I2

Is2 = 10 Is1

The voltage across R is VBB1-VBB2

VBE = VT In (Ic Is)

$$V_{BEI} - V_{BE2} = V_T \ln \left( \frac{I_{c1}}{I_{SI}} \right) - V_T \ln \left( \frac{I_{c2}}{I_{S2}} \right)$$

$$= V_T \left[ \ln \left( \frac{I_{c1}}{I_{SI}} \right) - \ln \left( \frac{I_{c2}}{I_{S2}} \right) \right]$$

$$= V_T \ln \left( \frac{I_{c1}}{I_{SI}} \times \frac{I_{S2}}{I_{c2}} \right)$$

= V, la (Isz X Ici)

= V7 RA (10 × 10)

= 0.025 RA(100)

= 0.115 1292546

≈ 0.115

$$I_{c2} \approx I_{E2} = \frac{V_{8E1} - V_{8E2}}{R}$$

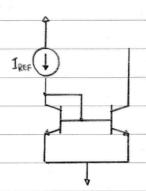
$$= \frac{0.115}{1000}$$

= 115 MA

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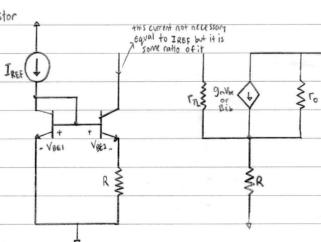
## a simple current mirror can be constructed as below:



How good is this current mirror depends on across the terminal, what is output resistance

t autput resistance = ro





output resistance = (1+9mVbe) ro

VBEI = VBE2 + VR

VR = VBEI - VBEZ

$$I_{c} = I_{S} e^{\left(\frac{V_{BE}}{V_{A}}\right)} \left(1 + \frac{V_{CE}}{V_{A}}\right)$$

$$I_{c} / \left(1 + \frac{V_{CE}}{V_{A}}\right) = I_{S} e^{\left(\frac{V_{BE}}{V_{T}}\right)}$$

$$I_{c} / \left(1 + \frac{V_{CE}}{V_{A}}\right), I_{S} = e^{\left(\frac{V_{BE}}{V_{T}}\right)}$$

$$I_c/(1+\frac{V_{CE}}{V_A}), I_s = e^{(\frac{V_{BE}}{V_T})}$$

$$ln\left(\frac{Ic}{Is}, \frac{1}{1+\frac{Vc\xi}{VA}}\right) = \frac{V\delta\xi}{VT}$$

$$V_{gE} = V_{T} \ln \left( \frac{I_{c}}{I_{s}} \cdot \frac{1}{1 + \frac{V_{cE}}{V_{A}}} \right)$$

$$V_{T} = \frac{kT}{2}$$